

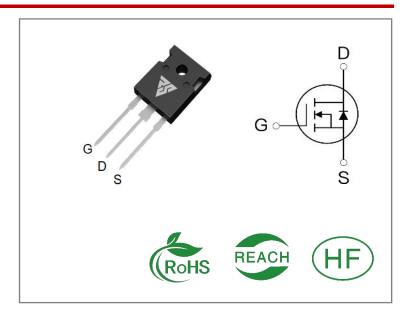
ID	R _{DS} (ON)(Typ)	VDSS
45A	0.08Ω	500V

Applications:

- Switch Mode Power Supply(SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

Features:

- Fast switching speed
- 100% avalanche tested
- Improved dv/dt capability



Ordering Information

Part Number	Package	Marking	Packing	Qty.
RS45N50W	T0-247-3	RS45N50W	Tube	30 PCS

Absolute Maximun Ratings Tc= 25℃ unless otherwise specified

Symbol	Parameter	RS45N50W	Units
VDSS	Drain-to-Source Voltage	500	V
ID	Continuous Drain Current TC=25℃	45	^
IDM	Pulsed Drain Current (Note*1)	180	Α
PD	Power Dissipation	260	W
VGS	Gate- to- Source Voltage	±30	V
EAS	Single Pulse Avalanche Engergy L = 10mH,,VDD = 50V, RG = 25 Ω	3125	mJ
	Maximum Temperature for Soldering		
TL TPKG	Leads at 0.063in(1.6mm)from Case for 10 seconds Package Body for 10 seconds	300 260	${\mathbb C}$
TJ and TSTG	Operating Junction and Storage Temperature Range	-55 to 150	

^{*} Drain Current Limited by Maximum Junction Temperature

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" Table may cause permanent damage to the device.



Thermal Resistance

Symbol	Parameter	RS45N50W	Units	Test Conditions
RÐJC	Junction-to-Case	0.48	°C/W	Drain lead soldered to water cooled heatsink, PD adjusted for a peak junction temperature of + 1 5 0 $^{\circ}\mathrm{C}$
RθJA	Junction-to- Ambient	62.5		1 cubic foot chamber,free air.

OFF Characteristics TJ= 25°C unless otherwise specified

Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
BVDSS	Drain- to- source Breakdown Voltage	500			V	VGS=0V,ID=250μ A
IDSS	Drain- to- Source Leakage Current			1	μΑ	VDS=500V,VGS= 0V
IGSS	Gate- to- Source Forward Leakage			100	- A	VGS=30V ,VDS=0 V
1033	Gate- to- Source Reverse Leakage			-100	nA	VGS=-30V ,VDS= 0V

ON Characteristics TJ=25°C unless otherwise specified

Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
RDS(on)	Static Drain- to- Source On- Resistance(Note*2)		0.08	0.1	Ω	VGS=10V,ID=22. 5A
VGS(TH	Gate Threshold Voltage	3		4	٧	VGS=VDS,ID=25 0μA

Resistive Switching Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
td(ON)	Turn- on Delay Time		84			
trise	Rise Time		87			VDS=250V
td(OFF)	Turn- OFF Delay Time		508		nS	ID=45A RG=25Ω
tfall	Fall Time		176			



Dynamic Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
Ciss	Input Capacitance		7000			VGS=0V
Coss	Output Capacitance		740		pF	VDS=25V
Crss	Reverse Transfer Capacitance		25			f=1.0MHz
Qg	Total Gate Charge		130			VDS=400V
Qgs	Gate- to- Source Charge		33		nC	ID=45A
Qgd	Gate-to-Drain(" Miller") Charge		42			VGS=10V

Source-Drain Diode Characteristics

Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
IS	Continuous Source Current			45	Α	Integral pn- diode
ISM	Maximum Pulsed Current			180	Α	in MOSFET
VSD	Diode Forward Voltage			1.4	V	IS=22.5A,VGS=0V
trr	Reverse Recovery Time		462		nS	VDD=250V
Qrr	Reverse Recovery Charge		8.5		μС	IS=45A,di/dt=100 A/μs

Notes:

^{* 1.} Repetitive rating, pulse width limited by maximum junction temperature.

^{* 2.} Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 1%



Typical Feature Curve

Figure 1. Output Characteristics (T_J = 25°C)

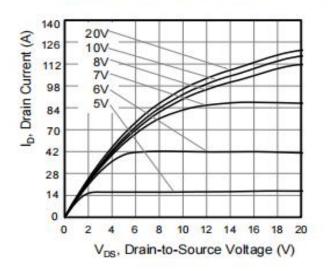


Figure 3. Drain Current vs. Temperature

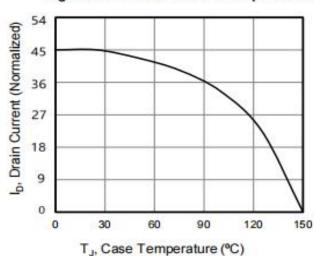


Figure 5. Transfer Characteristics

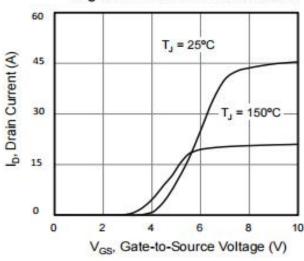


Figure 2. Body Diode Forward Voltage

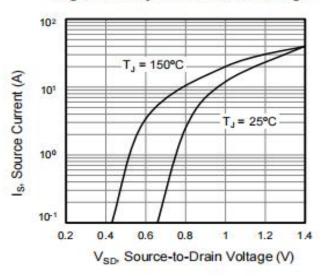


Figure 4. BV_{DSS} Variation vs. Temperature

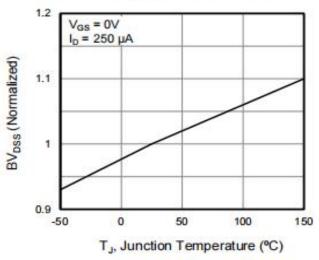
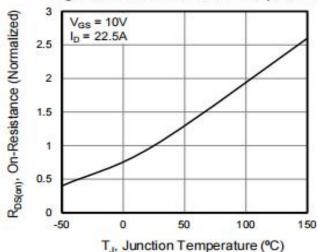
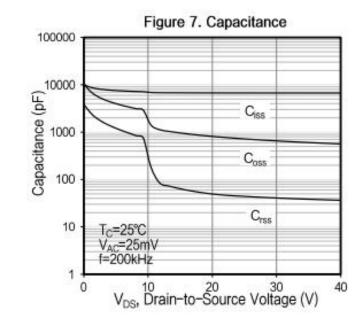
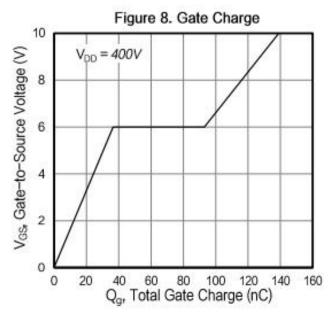


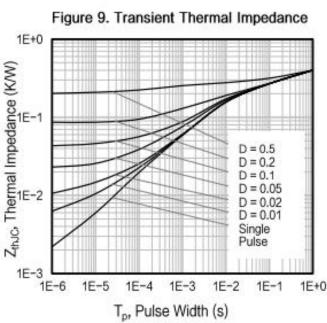
Figure 6. On-Resistance vs. Temperature

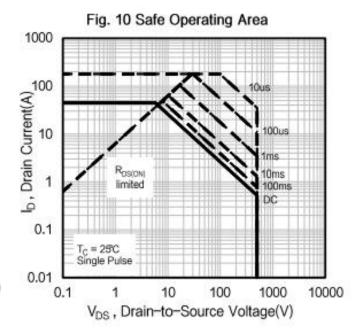














Test Circuits and Waveforms

Figure A: Gate Charge Test Circuit and Waveform

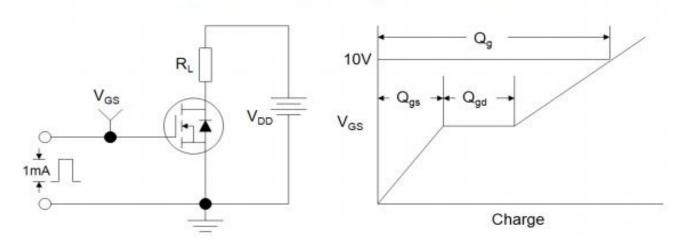


Figure B: Resistive Switching Test Circuit and Waveform

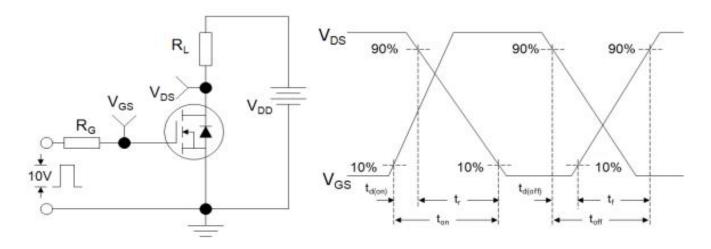
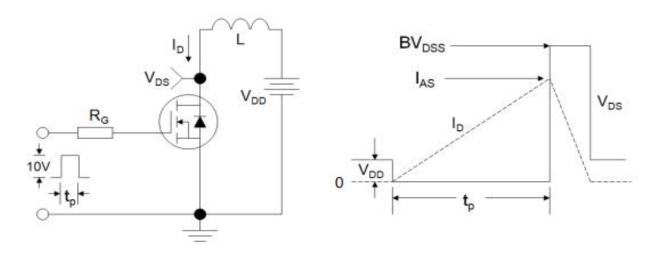
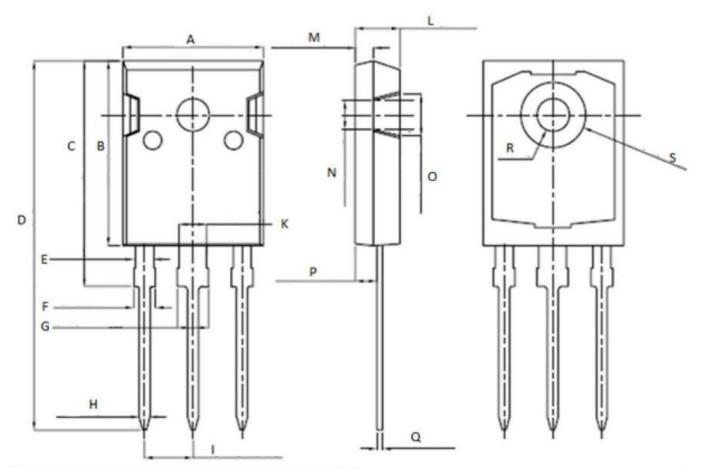


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





Package outline drawing(TO-247 Unit: mm)



	Unit: mm					
Symbol	Min.	Max.				
Α	15. 95	16. 25				
В	20.85	21. 25				
C	20.95	21. 35				
D	40.5	40.9				
E	1.9	2. 1				
F	2. 1	2. 25				
G	3. 1	3. 25				
Н	1.1	1.3				
	5. 40	5. 50				

Unit: mm					
Symbol	Min.	Max.			
K	2.90	3. 10			
L	4. 90	5. 30			
M	1.90	2.10			
N	4.50	4. 70			
0	5. 40	5. 60			
Р	2. 29	2.49			
Q	0.51	0. 71			
R	ф3.5	ф 3. 7			
S	ф7.1	ф7.3			



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DMN2080UCB4-7 DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 DMP22D4UFO-7B DMN1006UCA6-7 DMN16M9UCA6-7
STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 DMN2990UFB-7B
IPB80P04P405ATMA2 2N7002W-G MCAC30N06Y-TP MCQ7328-TP NTMC083NP10M5L NVMFS2D3P04M8LT1G BXP7N65D
BXP4N65F AOL1454G WMJ80N60C4 BXP2N20L BXP2N65D BXT1150N10J BXT1700P06M TSM60NB380CP ROG RQ7L055BGTCR
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